

Appl. No. 10/003,908  
Amdt dated August 13, 2004  
Reply to Office Action of May 19, 2004.

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listings of Claims:**

Claim 1: (currently amended) A method of operating a deposition process chamber, the method comprising:

placing a substrate in said process chamber;

depositing a film on said substrate, said depositing leaving a deposition residue on an interior surface of said chamber; and

cleaning said deposition residue from said interior surface by creating a fluorine-containing plasma in said chamber, said fluorine-containing plasma leaving a fluorine-containing contaminant on said interior surface; and thereafter removing said fluorine-containing contaminant by

supplying an oxygen-containing gas into the process chamber;

supplying a hydrogen-containing gas into the process chamber, said hydrogen-containing gas being different from said oxygen-containing gas;

producing a plasma comprising of a mixture of the oxygen-containing gas and the hydrogen-containing gas, thereby exothermically producing H<sub>2</sub>O;

causing so that the plasma to react reacts with the fluorine-containing contaminant to form a fluorine-containing material; and

removing the fluorine-containing material from the process chamber.

Claim 2: (previously presented) The method of claim 1, wherein the hydrogen-containing gas is selected from a group consisting of NH<sub>3</sub> and H<sub>2</sub>.

Claim 3: (previously presented) The method of claim 1, wherein the oxygen-containing gas is selected from a group consisting of N<sub>2</sub>O, O<sub>2</sub> and air.

Claim 4: (canceled)

Claim 5: (previously presented) The method of claim 1, wherein producing the plasma produces an ion flux to an interior surface of the process chamber, so that the ion

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flux results in an ion-enhanced chemical reaction between the plasma and the fluorine-containing contaminant.

**Claim 6:** (previously presented) The method of claim 1, wherein producing the plasma generates a plurality of coordinately and electronically unsaturated radicals and ions that react with the fluorine-containing contaminant.

**Claim 7:** (original) The method of claim 1, wherein the mixture of the oxygen-containing gas and the hydrogen-containing gas is 70 mol % N<sub>2</sub>O/NH<sub>3</sub>.

**Claim 8:** (original) The method of claim 7, wherein a flow rate of NH<sub>3</sub> into the process chamber is 1,500 sccm.

**Claim 9:** (original) The method of claim 7, wherein a flow rate of N<sub>2</sub>O into the process chamber is 3,500 sccm or less.

**Claim 10:** (original) The method of claim 7, wherein producing the plasma uses a high frequency RF power of 3,000W, and a pressure of the process chamber is 2 Torr.

**Claim 11:** (original) The method of claim 1, wherein the mixture of the oxygen-containing gas and the hydrogen-containing gas is 50 mol % N<sub>2</sub>O/NH<sub>3</sub>.

**Claim 12:** (original) The method of claim 11, wherein a flow rate of NH<sub>3</sub> into the process chamber is 1,500 sccm.

**Claim 13:** (original) The method of claim 11, wherein a flow rate of the N<sub>2</sub>O into the process chamber is 3,500 sccm or less.

**Claim 14:** (original) The method of claim 11, wherein producing the plasma uses a high frequency RF power of 3,000W, and a pressure of the process chamber is 2 Torr.

**Claim 15:** (original) The method of claim 1, wherein the mixture of the oxygen-containing gas and the hydrogen-containing gas is 52 mol % O<sub>2</sub>/NH<sub>3</sub>.

**Claim 16:** (original) The method of claim 15, wherein a flow rate of NH<sub>3</sub> into the process chamber is 2,000 sccm.

**Claim 17:** (original) The method of claim 15, wherein a flow rate of the N<sub>2</sub>O into the process chamber is 2,170 sccm or less.

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Claim 18: (original) The method of claim 15, wherein producing the plasma uses a high frequency RF power of 2,000W, and a pressure of the process chamber is 3 Torr.

Claim 19: (original) The method of claim 1, further comprising supplying an inert gas to stabilize the plasma.

Claim 20: (original) The method of claim 19, wherein the inert gas is selected from a group consisting of He, Ne, Ar, and Kr.

Claim 21: (original) The method of claim 1, wherein the process chamber is a chemical vapor deposition chamber.

Claim 22: (previously presented) The method of Claim 1 wherein the fluorine-containing material is a fluorine-containing gas.

Claim 23: (previously presented) The method of Claim 1 wherein the hydrogen-containing gas is NH<sub>3</sub> and the fluorine-containing material comprises an ammonium fluoride.

Claim 24: (currently amended) A method of operating a deposition process chamber, the method comprising:

placing a substrate in said process chamber;

depositing a film on said substrate, said depositing leaving a deposition residue on an interior surface of said chamber; and

cleaning said deposition residue from said interior surface by creating a fluorine-containing plasma in said chamber, said fluorine-containing plasma leaving a fluorine-containing contaminant on said interior surface; and thereafter removing said fluorine-containing contaminant by

creating a plasma that generates H<sub>2</sub>O and heat in said process chamber, said plasma H<sub>2</sub>O reacting with the fluorine-containing contaminant in the presence of said heat to form a fluorine-containing material; and

removing the fluorine-containing material from the process chamber.

Claim 25: (previously presented) The method of Claim 24 wherein the fluorine-containing material is a fluorine-containing gas.

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**Claim 26: (previously presented) The method of Claim 24 wherein the hydrogen-containing gas is NH<sub>3</sub> and the fluorine-containing material comprises an ammonium fluoride.**

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